

- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology



Product Summary

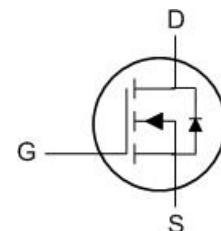
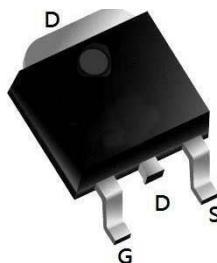
BVDSS	RDS(ON)	ID
40V	5.4mΩ	80A

Description

The XXW80N04B is the high cell density trenched N-ch MOSFETs, which provide excellent RDS(ON) and gate charge for most of the synchronous buck converter applications.

The XXW80N04B meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

TO252 Pin Configuration



Absolute Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter		Value	Units
V_{DS}	Drain-to-Source Voltage		40	V
V_{GS}	Gate-to-Source Voltage		± 20	V
I_D	Continuous Drain Current	$T_C = 25^\circ\text{C}$	80	A
		$T_C = 100^\circ\text{C}$	38	
I_{DM}	Pulsed Drain Current ⁽¹⁾		240	A
E_{AS}	Single Pulsed Avalanche Energy ⁽²⁾		100	mJ
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$	114	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁽³⁾		37	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case		1.1	
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 150	$^\circ\text{C}$

N-Ch 40V Fast Switching MOSFETs
Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

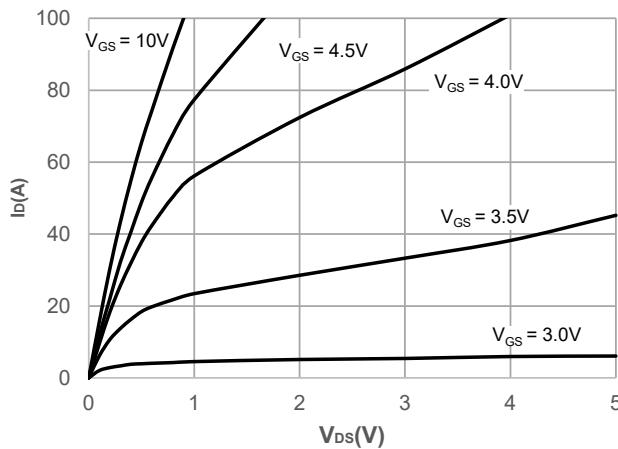
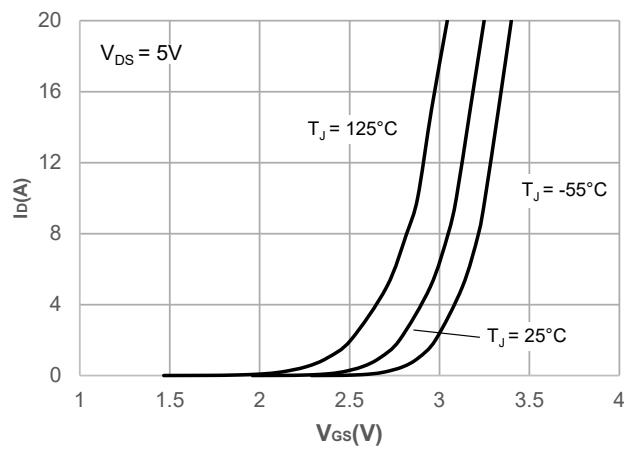
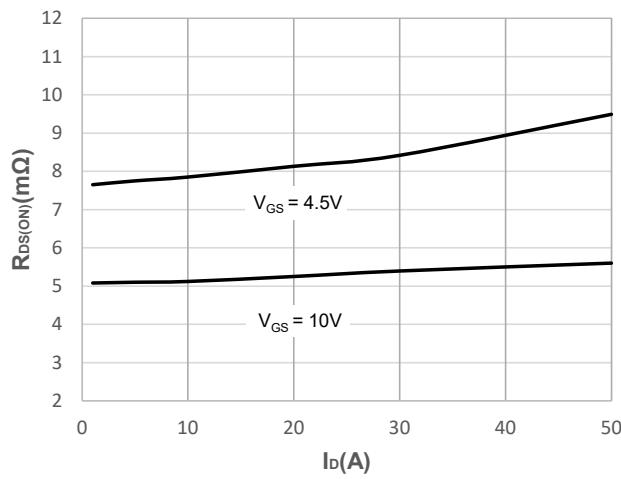
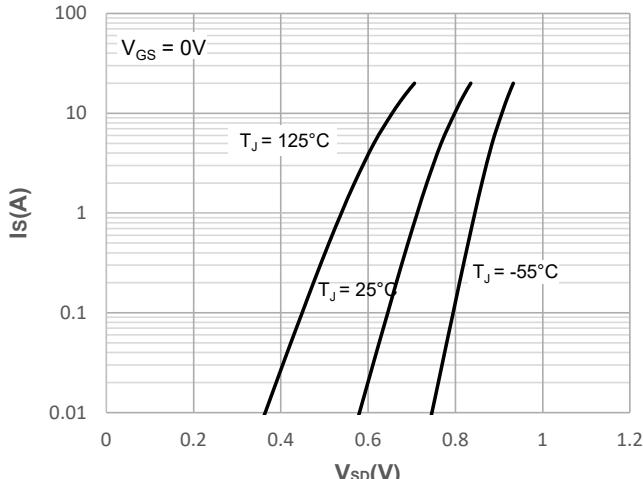
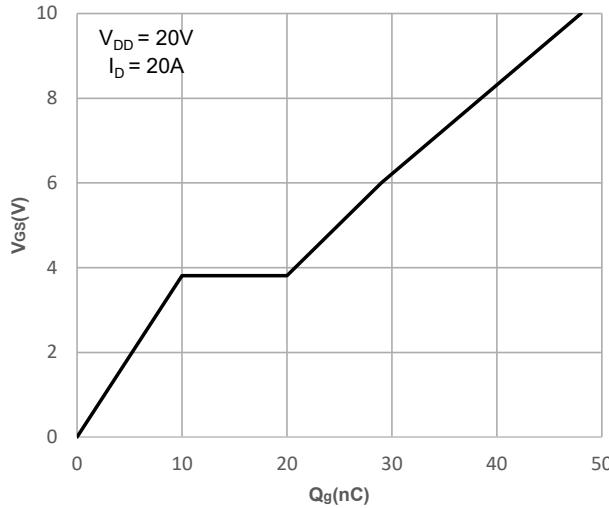
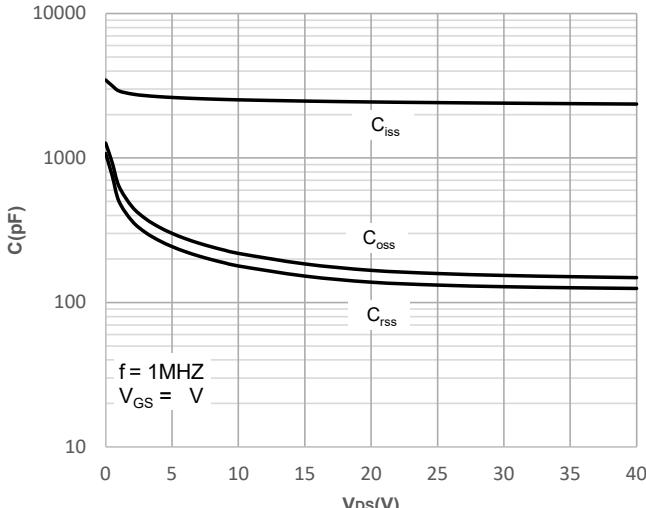
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	40	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 40\text{V}, V_{GS} = 0\text{V}$	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$	-	-	± 100	nA
On Characteristics						
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	1.3	1.9	2.5	V
$R_{\text{DS(ON)}}$	Static Drain-Source ON-Resistance ⁽⁴⁾	$V_{GS} = 10\text{V}, I_D = 30\text{A}$	-	5.4	7.0	$\text{m}\Omega$
		$V_{GS} = 4.5\text{V}, I_D = 20\text{A}$	-	8.1	10.5	$\text{m}\Omega$
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}, V_{DS} = 20\text{V}, f = 1\text{MHz}$	-	2443	-	pF
C_{oss}	Output Capacitance		-	167	-	pF
C_{rss}	Reverse Transfer Capacitance		-	138	-	pF
Q_g	Total Gate Charge	$V_{GS} = 0 \text{ to } 10\text{V}$ $V_{DS} = 20\text{V}, I_D = 20\text{A}$	-	48	-	nC
Q_{gs}	Gate Source Charge		-	10	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	10	-	nC
Switching Characteristics						
$t_{d(\text{on})}$	Turn-On Delay Time	$V_{GS} = 10\text{V}, V_{DD} = 20\text{V}$ $I_D = 20\text{A}, R_{\text{GEN}} = 3\Omega$	-	10	-	ns
t_r	Turn-On Rise Time		-	28	-	ns
$t_{d(\text{off})}$	Turn-Off Delay Time		-	40	-	ns
t_f	Turn-Off Fall Time		-	7	-	ns
Drain-Source Diode Characteristics and Max Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current	-	-	80	A	
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	240	A	
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = 30\text{A}$	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	$I_F = 20\text{A}, di/dt = 100\text{A/us}$	-	11	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	5	-	nC

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.

 2. E_{AS} condition: Starting $T_J = 25^\circ\text{C}$, $V_{DD} = 20\text{V}$, $V_G = 10\text{V}$, $R_G = 25\text{ohm}$, $L = 0.5\text{mH}$, $I_{AS} = 20\text{A}$

 3. $R_{\theta JA}$ is measured with the device mounted on a 1inch² pad of 2oz copper FR4 PCB

 4. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.

N-Ch 40V Fast Switching MOSFETs
Typical Performance Characteristics
Figure 1: Output Characteristics

Figure 2: Typical Transfer Characteristics

Figure 3: On-resistance vs. Drain Current

Figure 4: Body Diode Characteristics

Figure 5: Gate Charge Characteristics

Figure 6: Capacitance Characteristics


N-Ch 40V Fast Switching MOSFETs
Typical Performance Characteristics

Figure 7: Normalized Breakdown voltage vs. Junction Temperature

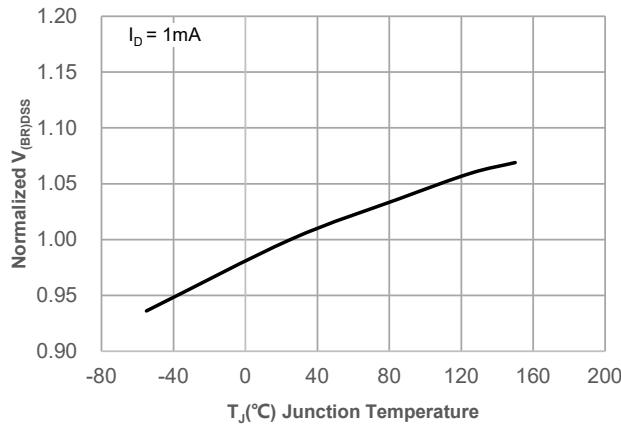


Figure 8: Normalized on Resistance vs. Junction Temperature

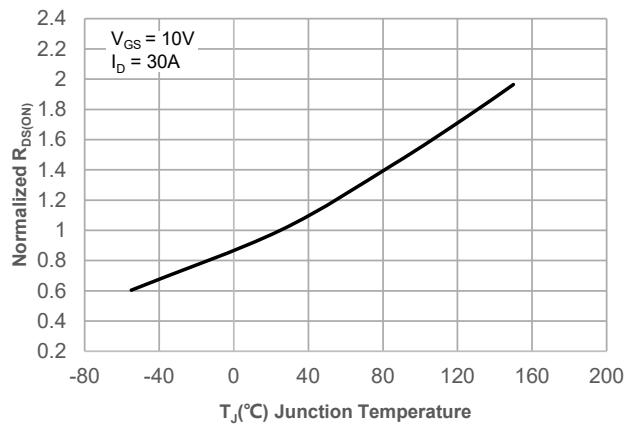


Figure 9: Maximum Safe Operating Area

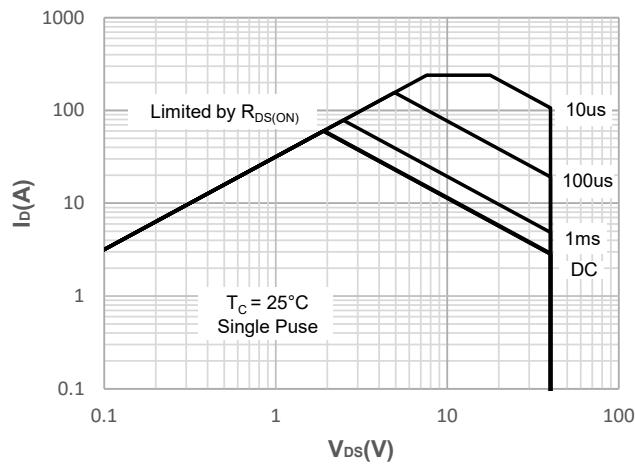


Figure 10: Maximum Continuous Drian Current vs. Case Temperature

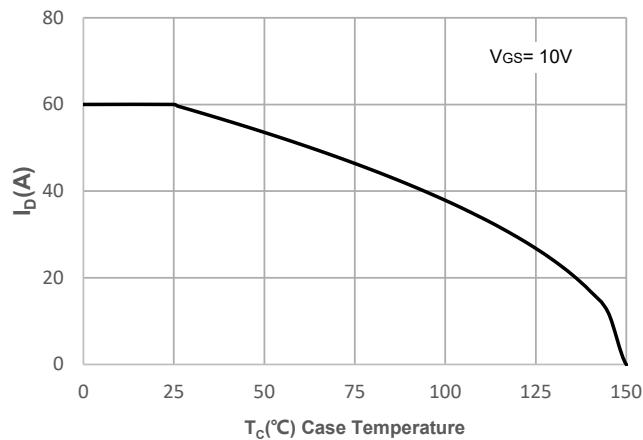


Figure 11: Normalized Maximum Transient Thermal Impedance

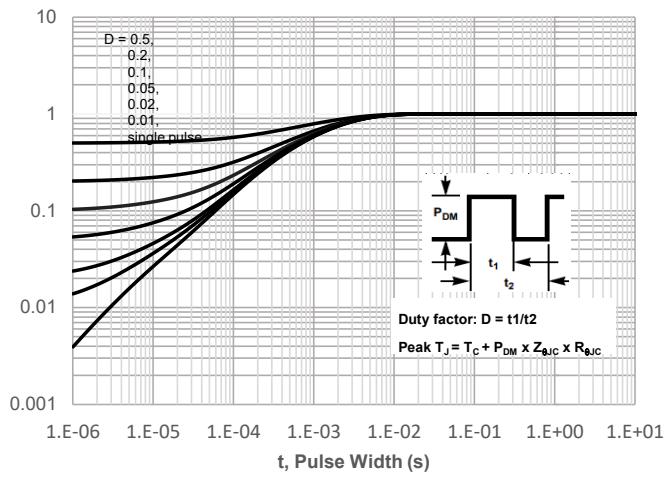
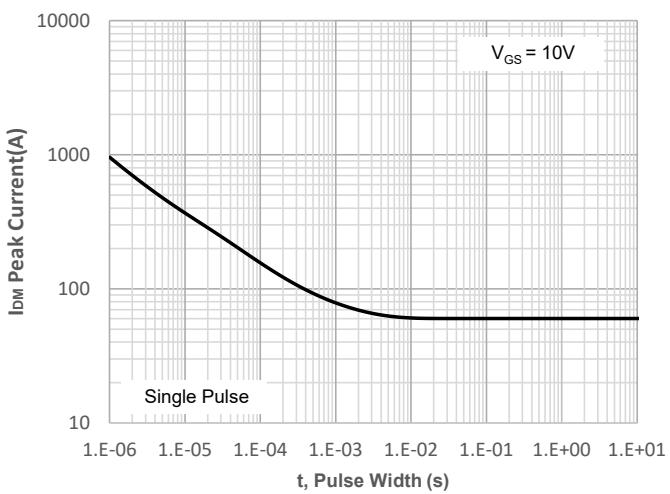


Figure 12: Peak Current Capacity



N-Ch 40V Fast Switching MOSFETs

Test Circuit

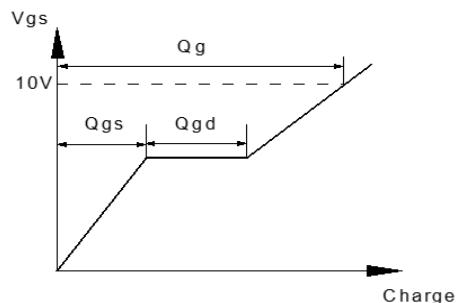
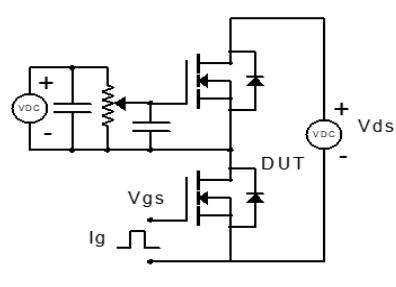


Figure 1: Gate Charge Test Circuit & Waveform

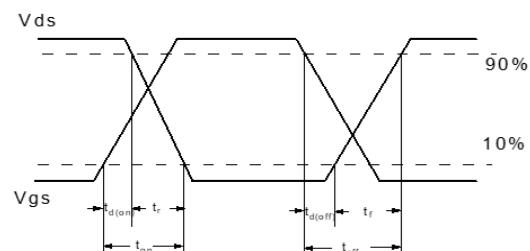
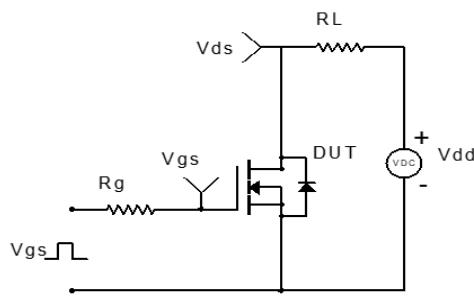


Figure 2: Resistive Switching Test Circuit & Waveform

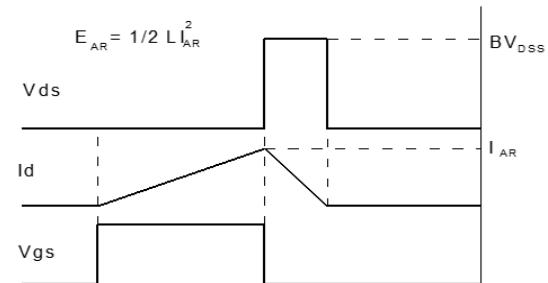
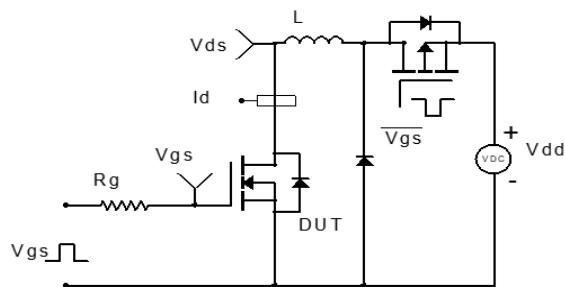


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

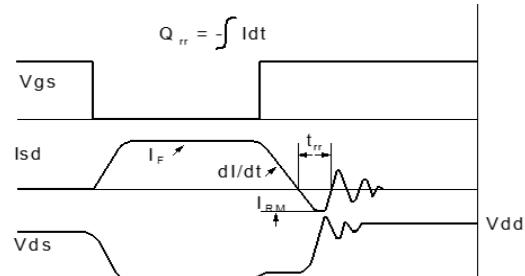
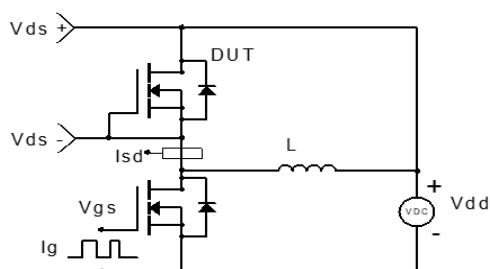
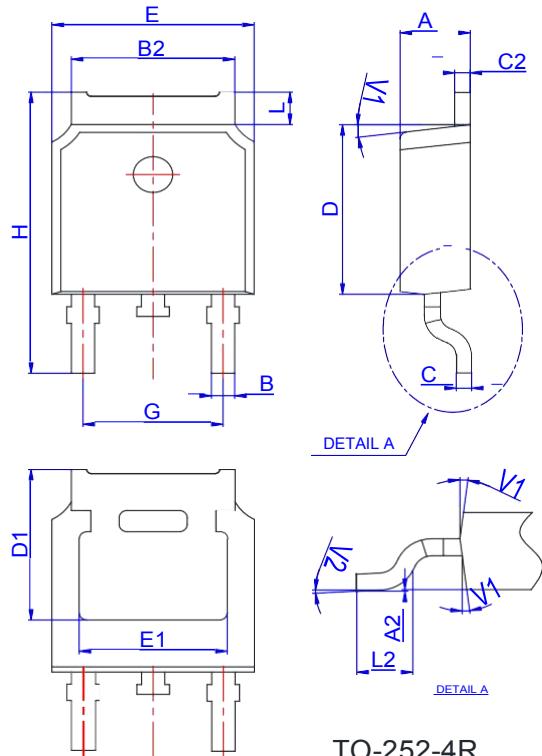


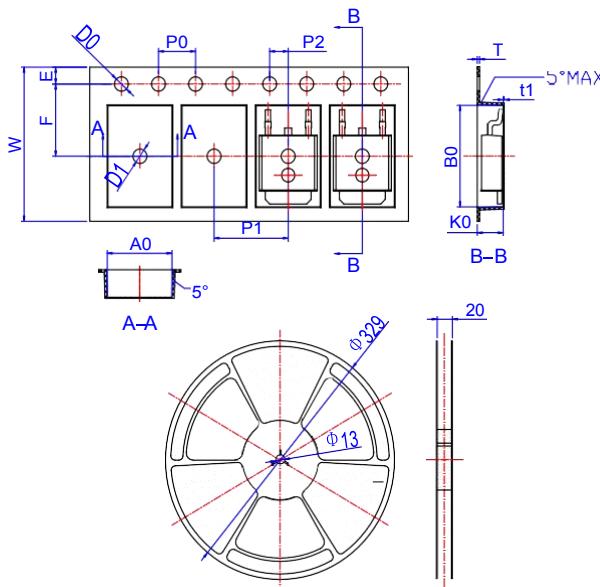
Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Specification-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583